

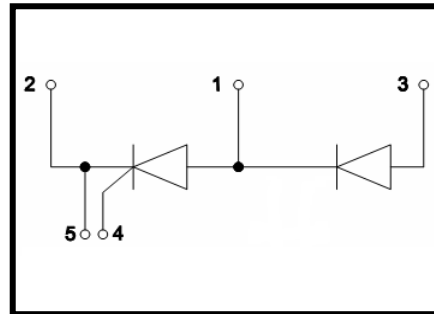
## Features

- Isolation Voltage 3000 V~
- Industrial Standard Package
- High Surge Capability
- Glass Passivated Chips
- Simple Mounting
- Electrically Isolated by DBC Ceramic



## Applications

- DC Motor Control and Drives
- Battery Charges
- Welders
- Power Converters
- Lighting Control
- Heat and Temperature Control



## Advantages

- Space and Weight Savings
- Improved Temperature and Power Cycling

## ■ Diode

### ABSOLUTE MAXIMUM RATINGS

$T_C=25^{\circ}\text{C}$  unless otherwise specified

Symbol	Test Condition	Value	Unit
$V_{RRM}$		1600	V
$I_{d(AV)}$	$T_C=100^{\circ}\text{C}$ , module	160	A
$I_{FSM}$	$T_J=45^{\circ}\text{C}$ ; $t=10\text{ms}$ (50Hz),sine	5160	A
	$V_R=0$ $t=8.3\text{ms}$ (60Hz),sine	5420	A
$I^2t$	$T_J=45^{\circ}\text{C}$ ; $t=10\text{ms}$ (50Hz),sine	133.1	$\text{KA}^2\text{s}$
	$V_R=0$ $t=8.3\text{ms}$ (60Hz),sine	121.9	$\text{KA}^2\text{s}$
$T_J$	Junction Temperature	-40~150	$^{\circ}\text{C}$

### ELECTRICAL AND THERMAL CHARACTERISTICS

$T_C=25^{\circ}\text{C}$  unless otherwise specified

Symbol	Test Condition	Value	Unit
$I_R$	$V_R=V_{RRM}$ ; $T_J=25^{\circ}\text{C}$	$\leq 0.5$	mA
	$V_R=V_{RRM}$ ; $T_J=T_{JM}$	$\leq 6$	mA
$V_F$	$I_F=500\text{A}$	1.50	V
$V_{T0}$	For power-loss calculations only	0.8	V
$R_{thJC}$	Thermal Resistance , Junction-to-Case	0.18	K/W
$R_{thCS}$	Thermal Resistance, Case -to-Sink	0.10	K/W

## ■ Thyristor

**ABSOLUTE MAXIMUM RATINGS**T<sub>C</sub>=25°C unless otherwise specified

Symbol	Test Condition	Value	Unit
V <sub>RRM</sub> /V <sub>DRM</sub>		1600	V
I <sub>T(AV)</sub>	T <sub>C</sub> =85°C, 180° conduction, half sine wave;	160	A
I <sub>T(RMS)</sub>	as AC switch;	355	A
I <sub>TSM</sub>	T <sub>J</sub> =45°C, t=10ms (50Hz), sine, V <sub>R</sub> =0;	3000	A
	T <sub>J</sub> =45°C, t=8.3 ms (60Hz), sine, V <sub>R</sub> =0;	3200	
I <sup>2</sup> t	T <sub>J</sub> =45°C, t=10ms (50Hz), sine, V <sub>R</sub> =0;	45	KA <sup>2</sup> s
	T <sub>J</sub> =45°C, t=8.3 ms (60Hz), sine, V <sub>R</sub> =0;	42.5	
I <sub>DRM</sub> /I <sub>RRM</sub>	V <sub>R</sub> =V <sub>RRM</sub> , V <sub>D</sub> =V <sub>DRM</sub> , gate open circuit;	0.5	mA
	T <sub>J</sub> =125°C, V <sub>R</sub> =V <sub>RRM</sub> , V <sub>D</sub> =V <sub>DRM</sub> , gate open circuit;	40	mA
dV/dt	T <sub>J</sub> =125°C, exponential to 67% rated V <sub>DRM</sub>	1000	V/us
V <sub>ISOL</sub>	50Hz, all terminals shorted, t=1min, I <sub>ISOL</sub> ≤1mA ;	3000	V~
T <sub>J</sub>	Max. junction operating temperature range	-40~125	°C
T <sub>STG</sub>	Max. storage temperature range	-40~125	°C

**ELECTRICAL CHARACTERISTICS**T<sub>C</sub>=25°C unless otherwise specified

Symbol	Test Condition	Min.	Typ.	Max.	Unit
V <sub>TO</sub>	16.7% x π x I <sub>AV</sub> < I < π x I <sub>AV</sub> , T <sub>J</sub> =125°C;			0.80	V
	I > π x I <sub>AV</sub> , T <sub>J</sub> =125°C;			0.98	V
r <sub>t</sub>	16.7% x π x I <sub>AV</sub> < I < π x I <sub>AV</sub> , T <sub>J</sub> =125°C;			1.67	mΩ
	I > π x I <sub>AV</sub> , T <sub>J</sub> =125°C;			1.38	mΩ
I <sub>H</sub>	V <sub>AK</sub> = 6V, initial I <sub>T</sub> =30A;			200	mA
I <sub>L</sub>	Anode supply =6V, resistive load=1Ω, gate pulse =10V, 100us;			400	mA
V <sub>TM</sub>	I <sub>TM</sub> =500A, t <sub>d</sub> =10 ms, half sine;		1.54	2.0	V
P <sub>GM</sub>	t <sub>p</sub> ≤5ms, T <sub>J</sub> =125°C;			12	W
P <sub>GM(AV)</sub>	f=50Hz, T <sub>J</sub> =125°C;			3	W
I <sub>GM</sub>	t <sub>p</sub> ≤5ms, T <sub>J</sub> =125°C;			3	A
-V <sub>GT</sub>				10	V
V <sub>GT</sub>	V <sub>A</sub> =6V, R <sub>A</sub> =1Ω, T <sub>J</sub> =-40°C;			4	V
	V <sub>A</sub> =6V, R <sub>A</sub> =1Ω;			2.5	
	V <sub>A</sub> =6V, R <sub>A</sub> =1Ω, T <sub>J</sub> =125°C;			1.7	
I <sub>GT</sub>	V <sub>A</sub> =6V, R <sub>A</sub> =1Ω, T <sub>J</sub> =-40°C;			270	mA
	V <sub>A</sub> =6V, R <sub>A</sub> =1Ω;			150	
	V <sub>A</sub> =6V, R <sub>A</sub> =1Ω, T <sub>J</sub> =125°C;			80	
V <sub>GD</sub>	V <sub>AK</sub> =V <sub>DRM</sub> , T <sub>J</sub> =125°C			0.3	V
I <sub>GD</sub>				10	mA
di/dt	I <sub>TM</sub> =400A, rated V <sub>DRM</sub> , T <sub>J</sub> =125°C			300	A/us

**THERMAL AND MECHANICAL CHARACTERISTICS**

$T_C=25^{\circ}\text{C}$  unless otherwise specified

Symbol	Test Condition	value	Unit
$R_{thjc}$	DC operation, per junction;	0.18	K/W
$R_{THCS}$	Mounting surface smooth, flat and greased, per junction;	0.1	K/W
Md	Mounting torque(M6)	3 ~ 5	N·m
	Terminal connection torque(M6)		
Weight	Typical value	156	g

**Characteristic curves**

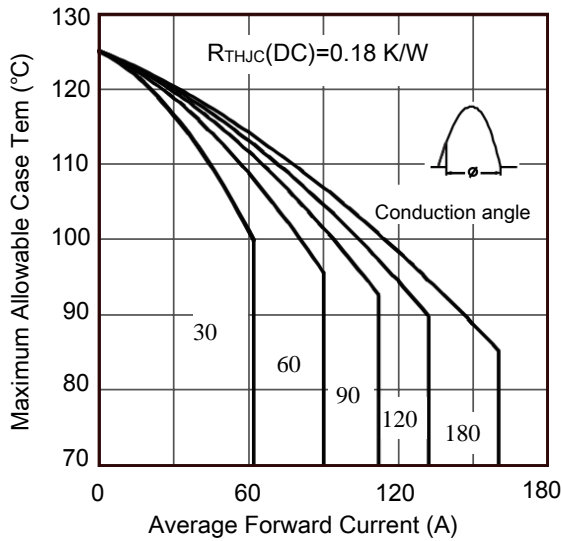


Figure 1. Current Rating Characteristics

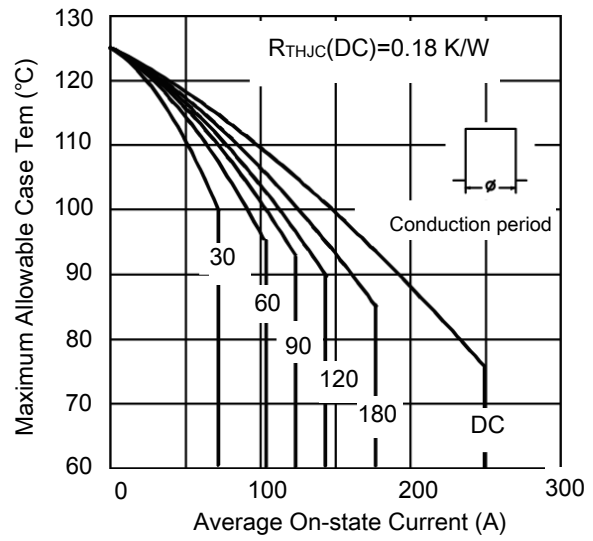


Figure 2. Current Rating Characteristics

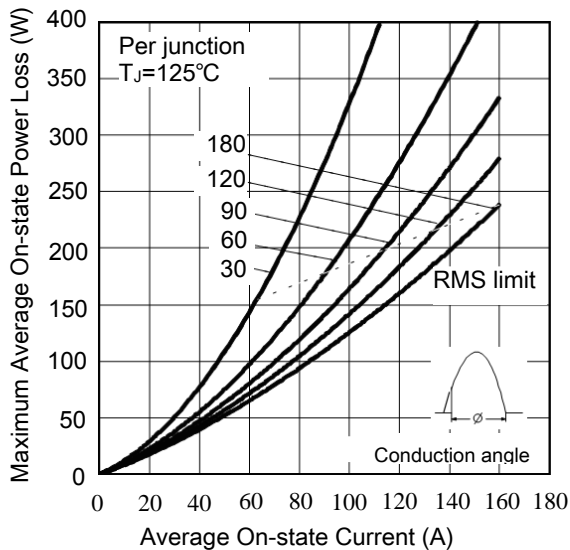


Figure 3. On-state Power Loss Characteristics

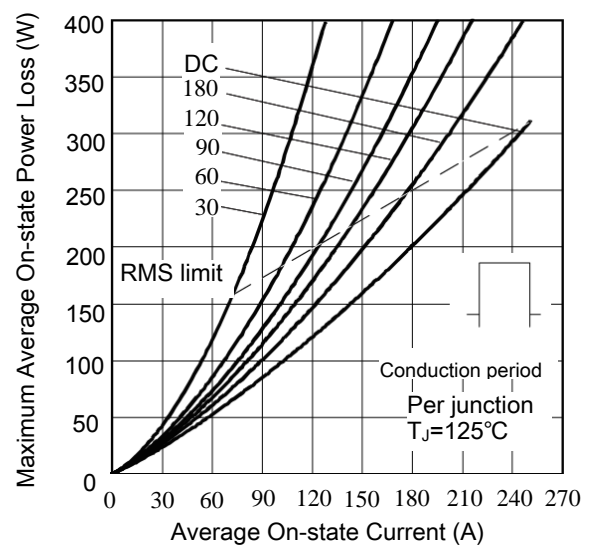
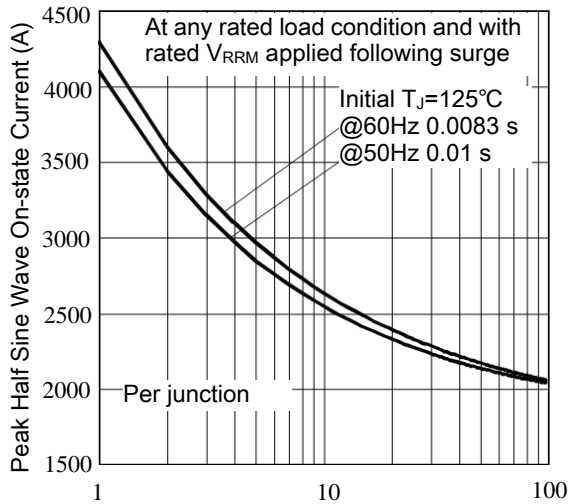


Figure 4. On-state Power Loss Characteristics



Number Of Equal Amplitude Half Cycle Current Pulses (N)  
Figure 5. Maximum Non-Repetitive Surge Current

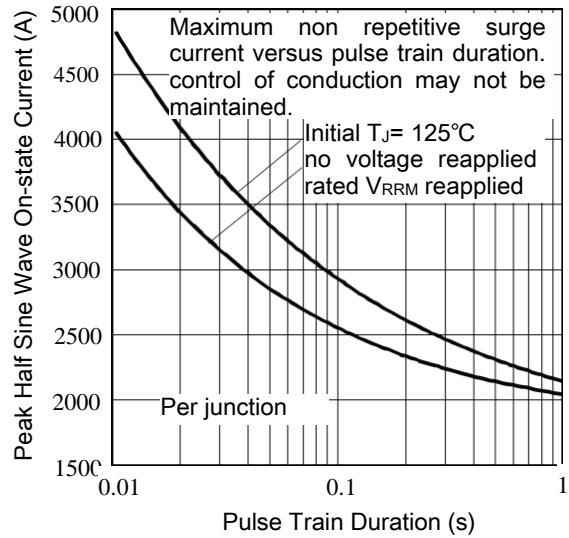


Figure 6. Maximum Non-Repetitive Surge Current

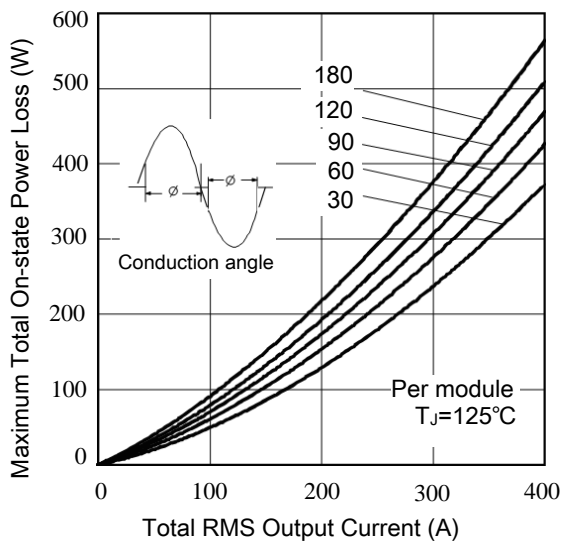


Figure 7. On-State Power Loss Characteristics-1

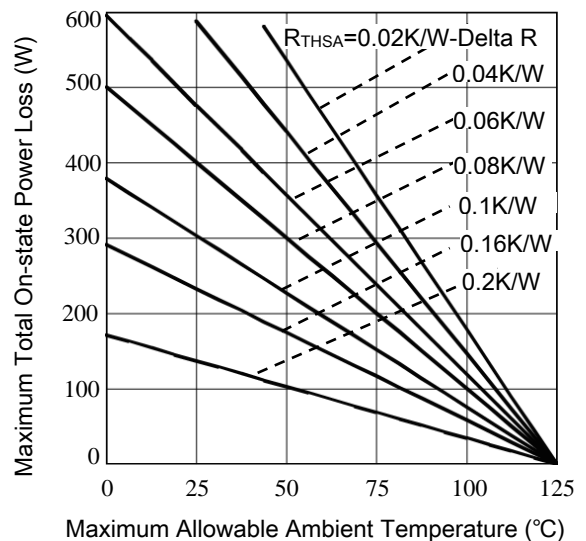


Figure 8 On-State Power Loss Characteristics-2

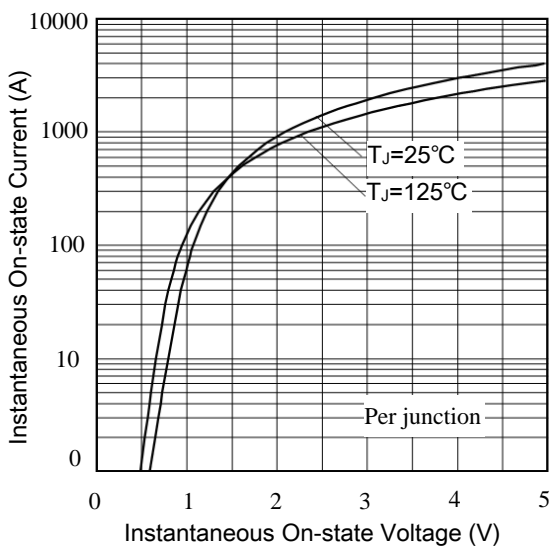


Figure 9. On State Voltage Drop Characteristics

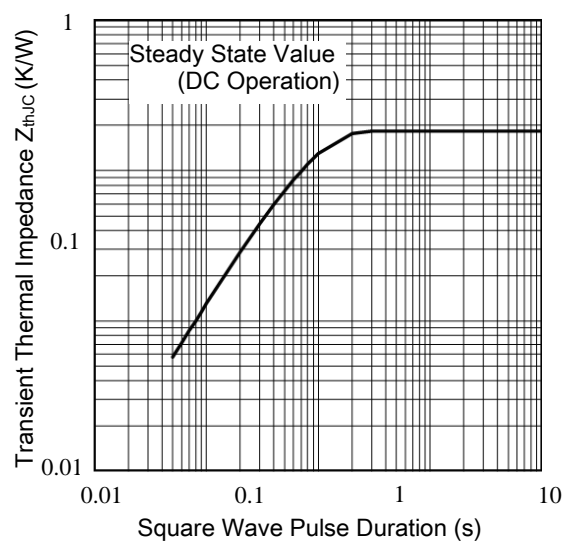


Figure 10. Thermal Impedance  $Z_{thJC}$  Characteristics

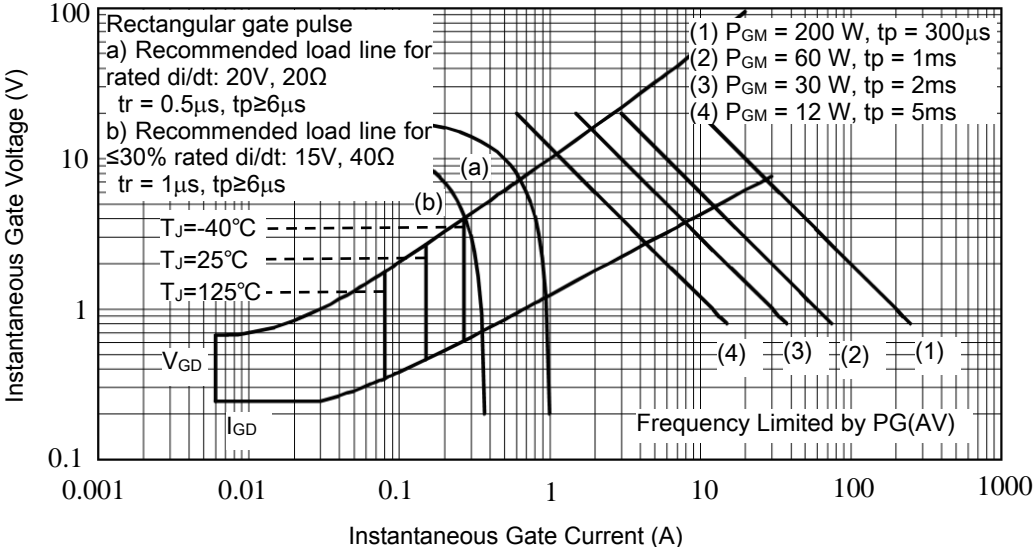


Figure 11. Gate Characteristics

Package Outline (Dimensions in mm)

